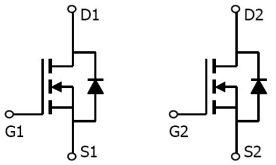
AP4008QD

N-Channel Power Mosfet

DATA SHEET

Feature

- 40V,20A
  $R_{DS(ON)}$ <22mΩ @V_{GS}=10V
  $R_{DS(ON)}$ <30mΩ @V_{GS}=4.5V
- Trench DMOS Power MOSFET
- Fast Switching
- Exceptional on-resistance and maximum DC current capability



Schematic diagram

Marking and pin assignment

Application

- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
4008QD	AP4008QD	PDFN3X3	13 inch	-	5000

ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current (T_a =25℃)	I_D	20	A
Continuous Drain Current (T_a =100℃)	I_D	13	A
Pulsed Drain Currenr [1]	I_{DM}	48	A
Power Dissipation	P_D	21	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	6.25	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	40	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} =40V, V_{GS} = 0V	-	-	1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±20V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage(2)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	1	1.6	2.5	V
Drain-source on-resistance(2)	$R_{DS(on)}$	V_{GS} =10V, I_D =10A	-	17	22	mΩ
		V_{GS} =4.5V, I_D =6A	-	22	30	
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =20V, V_{GS} =0V, f =1MHz	-	1050	-	pF
Output Capacitance	C_{oss}		-	84	-	
Reverse Transfer Capacitance	C_{rss}		-	72	-	
Switching characteristics						
Turn-on delay time	$t_{d(on)}$	V_{DD}=20V, R_L=1.5Ω V_{GS}=10V, R_G=3Ω	-	11	-	ns
Turn-on rise time	t_r		-	13	-	
Turn-off delay time	$t_{d(off)}$		-	36	-	
Turn-off fall time	t_f		-	9	-	
Total Gate Charge	Qg	VDS=20V, ID=5A, VGS=10V	-	11	-	nC
Gate-Source Charge	Qgs		-	1.9	-	
Gate-Drain Charge	Qgd		-	2.2	-	
Source-Drain Diode characteristics						
Diode Forward voltage(2)	V_{DS}	V_{GS} =0V, I_S=10A	-	-	1.2	V
Diode Forward current(3)	I_S		-	-	40	A

Notes:

1. Repetitive Rating: pulse width limited by maximum junction temperature
2. Pulse Test: pulse width≤300μs, duty cycle≤2%
3. Surface Mounted on FR4 Board,t≤10 sec

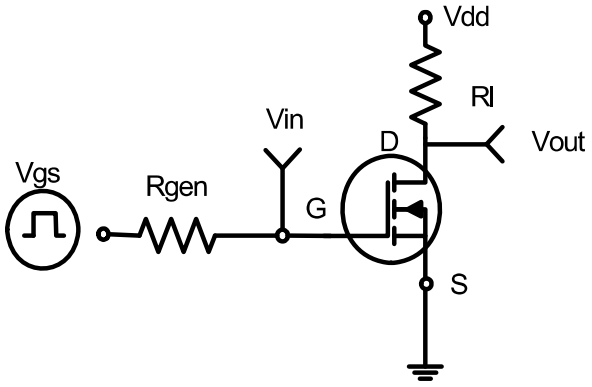


Figure 1:Switching Test Circuit

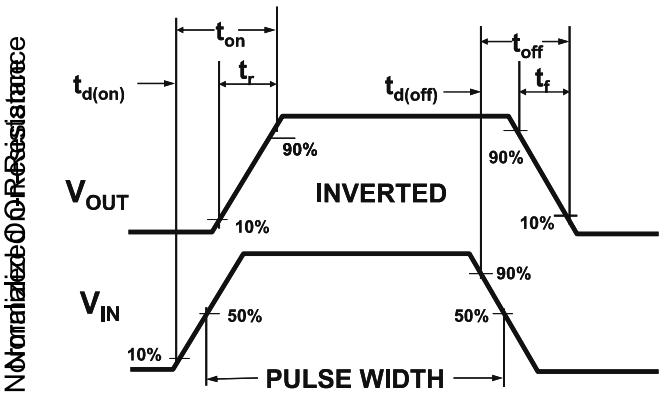
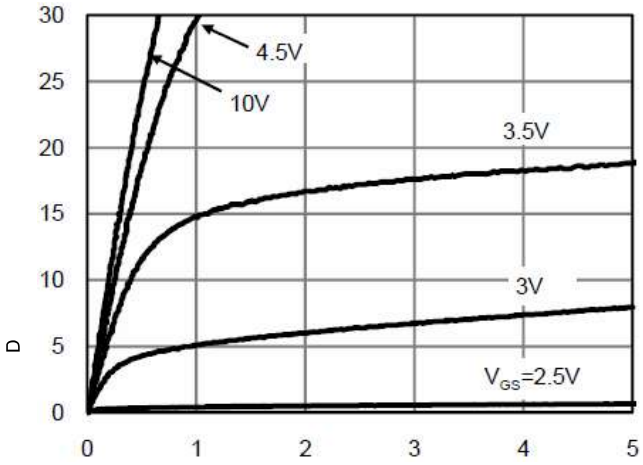
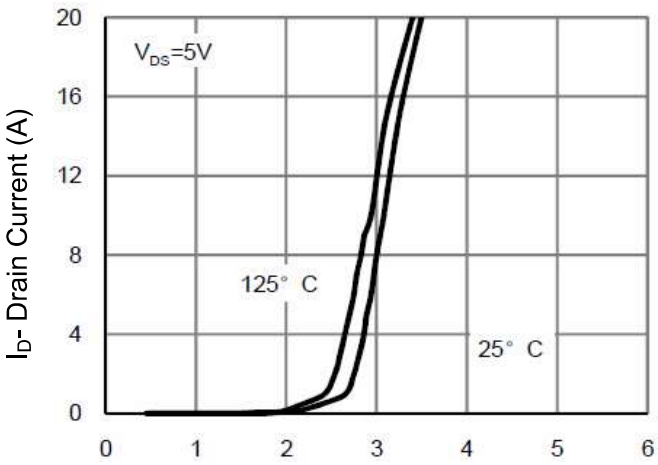


Figure 2:Switching Waveforms



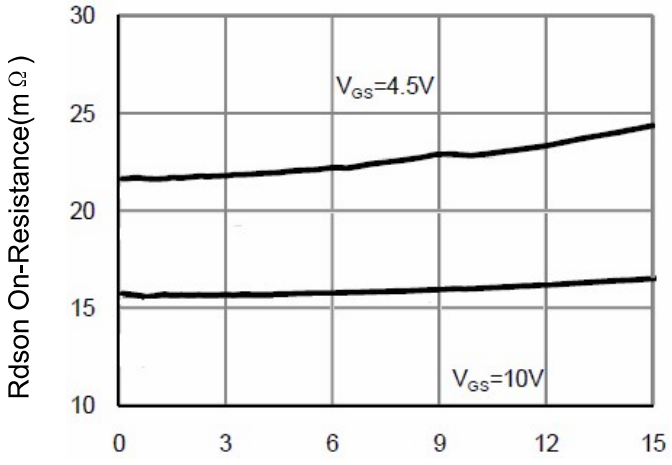
Vds Drain-Source Voltage (V)

Figure 3 Output Characteristics



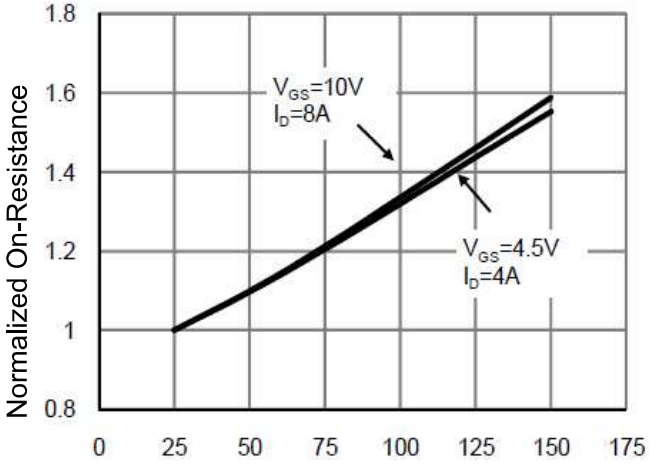
Vgs Gate-Source Voltage (V)

Figure 4 Transfer Characteristics



I_D- Drain Current (A)

Figure 5 Drain-Source On-Resistance



T_J-Junction Temperature(℃)

Figure 6 Drain-Source On-Resistance

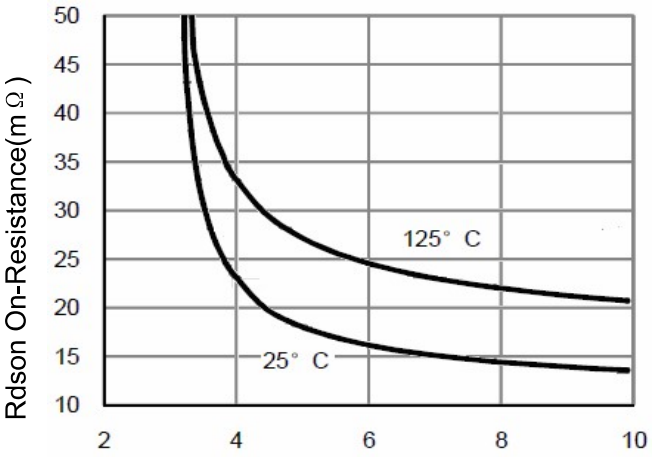


Figure7 Rdson vs Vgs

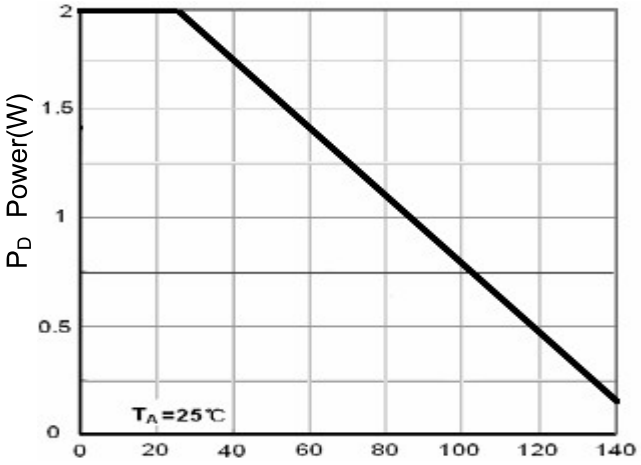


Figure 8 Power Dissipation

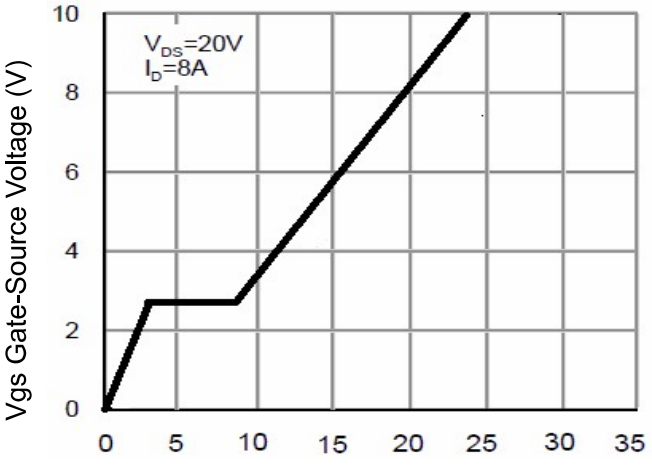


Figure 9 Gate Charge

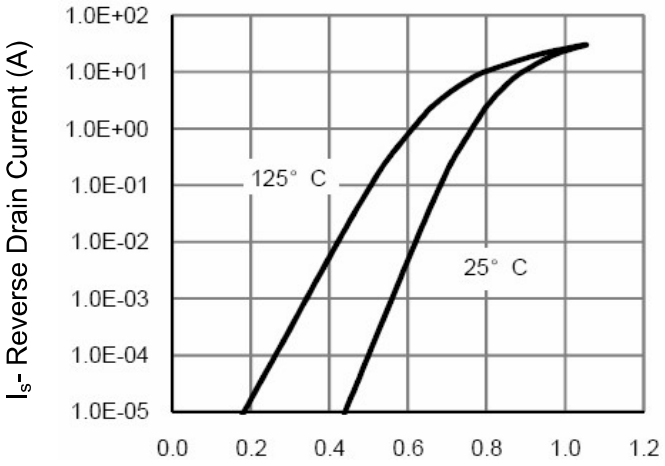


Figure 10 Source- Drain Diode Forward

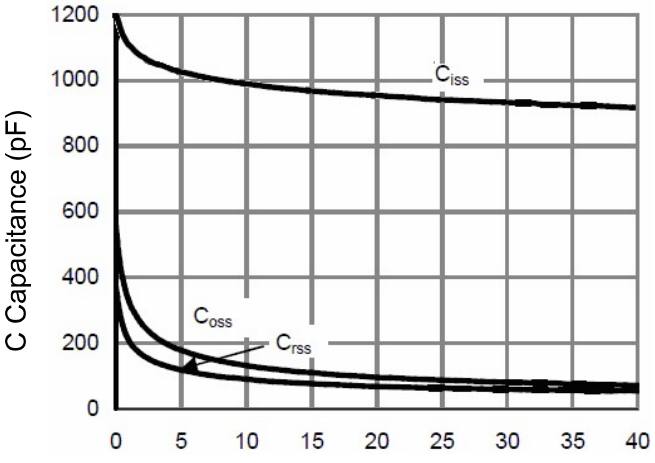


Figure 11 Capacitance vs Vds

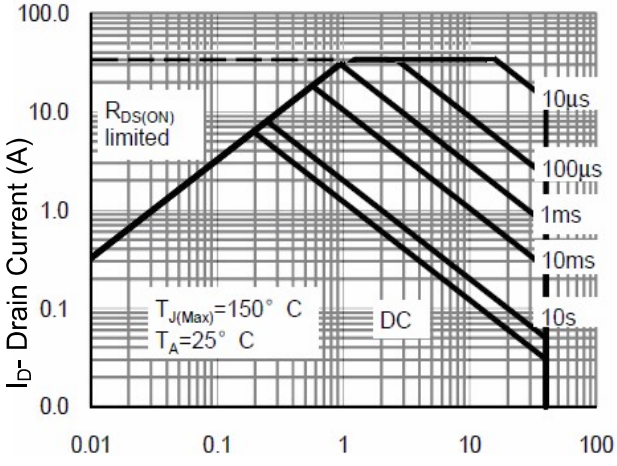
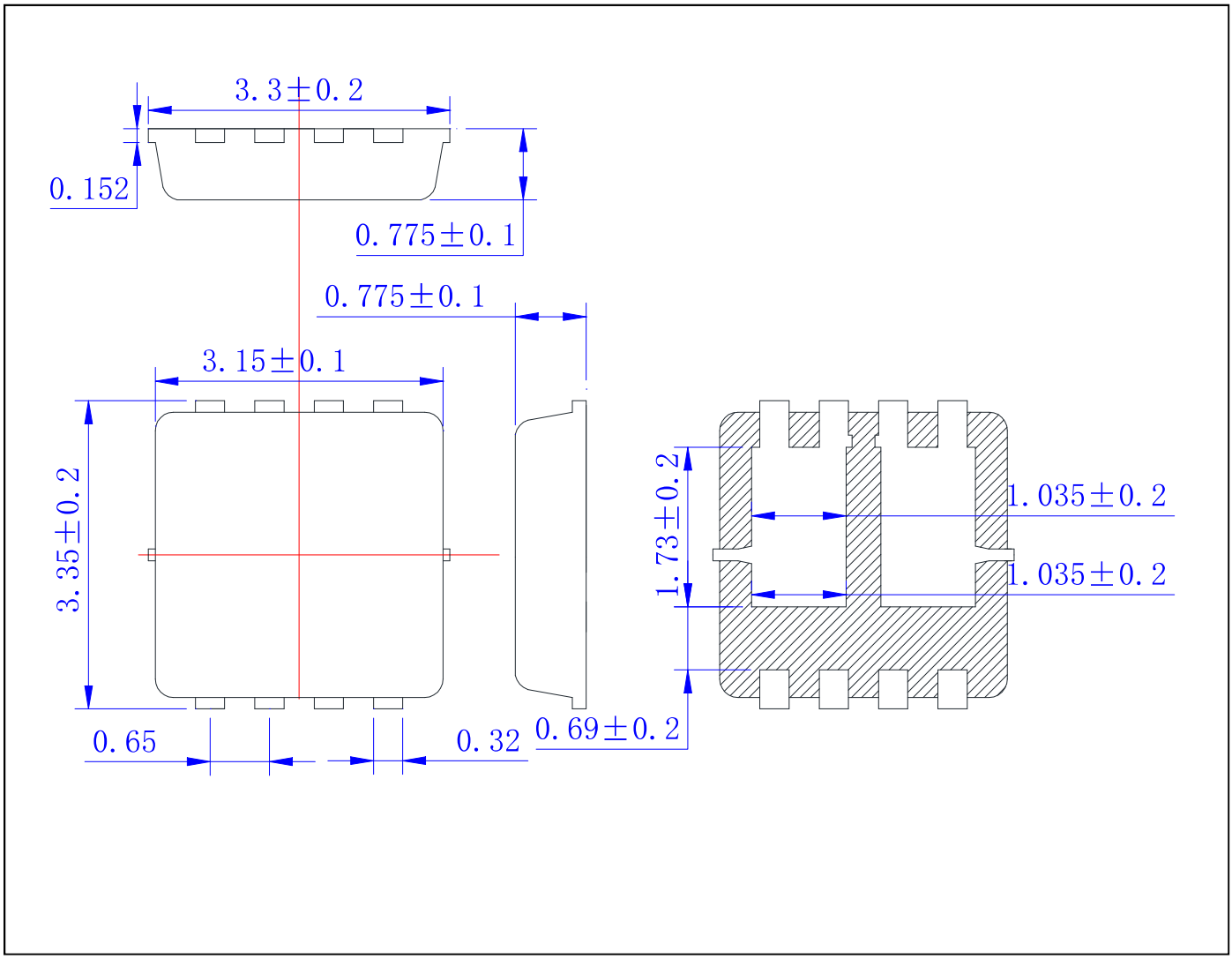


Figure 12 Safe Operation Area

PACKAGE OUTLINE DIMENSIONS



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